ABSTRACT OF THE DISCLOSURE

SEMICONDUCTOR ELEMENT, SEMICONDUCTOR ELEMENT FABRRICATING METHOD, SEMICONDUCTOR DEVICE, AND SEMICONDUCTOR DEVICE FABRICATING METHOD

A method of forming a bump electrode on an IC electrcde includes the steps of forming a ball bcnd on an IC electrode by a wire bonding apparatus, moving up a bonding capillary, moving the bonding capillary sideway and then downward, bonding an Au wire to the ball bond portion, and cutting the Au wire, the Au wire being prevented from coming in contact with the periphery of the ball bond portion except for the ball bond portion by presetting a descent position of the bonding capillary to a position higher than a position in which the ball bond is formed.

Figure 1B